

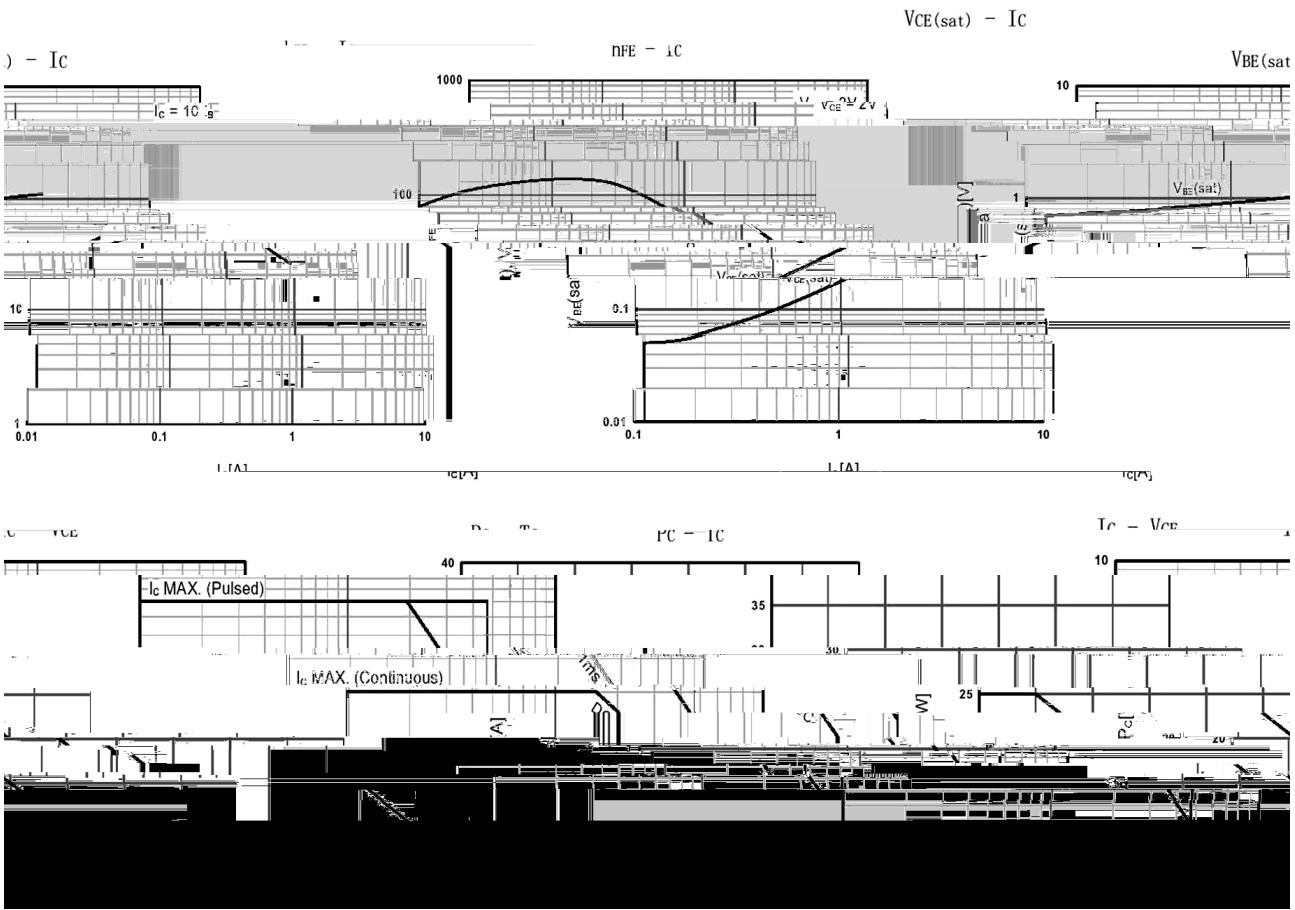


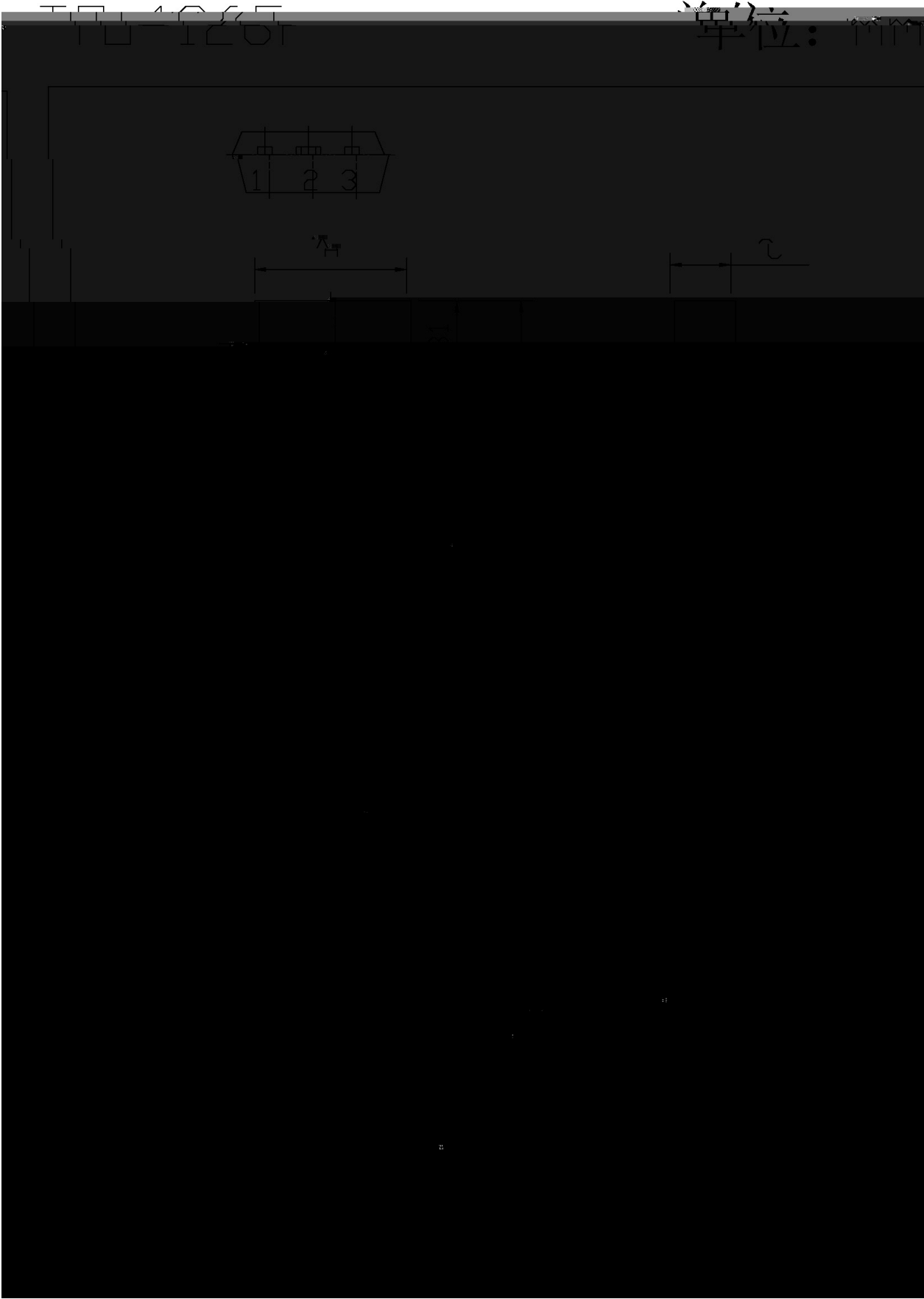
Rev.E Mar.-2016

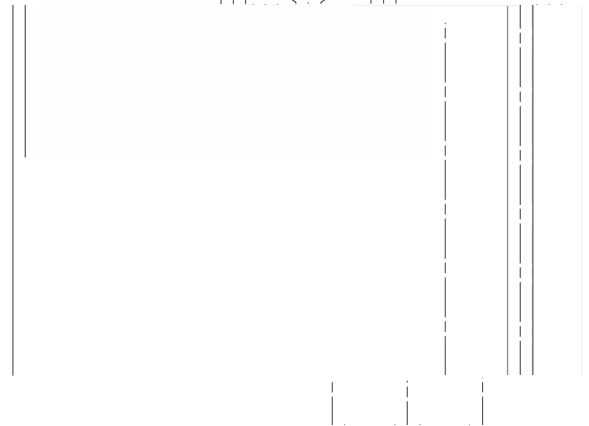
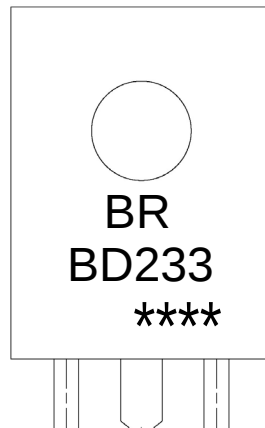
TO-126F	NPN	Silicon NPN transistor in a TO-126F Plastic Package.
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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	45	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	2.0	A
Collector Current – Continuous(Pulse)	I_{CP}	6.0	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ\text{C})$	25	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=100\text{mA}$ $I_B=0$	45			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=45\text{V}$ $I_E=0$			100	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0\text{V}$ $I_C=0$			1.0	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2.0\text{V}$ $I_C=150\text{mA}$	40		400	
	$h_{FE(2)}$	$V_{CE}=2.0\text{V}$ $I_C=1.0\text{A}$	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.0\text{A}$ $I_B=0.1\text{A}$			0.6	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=2.0\text{V}$ $I_C=1.0\text{A}$			1.3	V
Transition Frequency	f_T	$V_{CE}=10\text{V}$ $I_C=250\text{mA}$	3.0			MHz







BR

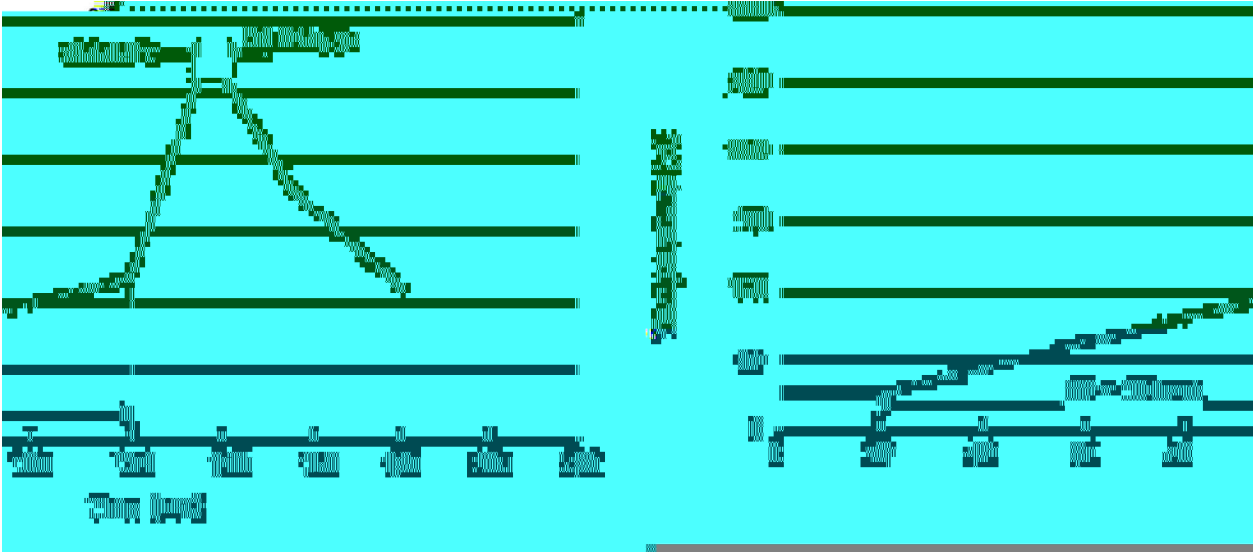
BD233

Note:

BR: Company Code

BD233: Product Type.

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.